L Number	Hits	Search Text	DB	Time stamp
1	2	("6348725").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 10:36
2	1671	mem with switch	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 10:37
3	174	mem with switch and etch$3 and intermediate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 10:39
4	0	mem with switch and etch$3 and intermediate and Tialn	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 10:40
5	174	intermediate and Tialn	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 10:41
6	29	intermediate near33 Tialn	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:19
7	0	sun.in. and li.in. and redeker.in	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:19
8	14497	sun.in. li.in. and redeker.in	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:20
9	682	sun.in. and li.in. redeker.in	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:20
10	52813	sun.in. li.in. redeker.in	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:20
11	25	(sun.in. li.in. redeker.in) and CU and CMP and amine	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:21
12	103	(sun.in. li.in. redeker.in) and CU and CMP	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:21
13	93	(sun.in. li.in. redeker.in) and CU and CMP and polish$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:21
14	25	(sun.in. li.in. redeker.in) and CU and CMP and polish$3 and amine	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:22

15	63	(sun.in. li.in. redeker.in) and CU and CMP and polish$3 and pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:22
16	431105	(sun.in. li.in. redeker.in) and CU and CMP and polish$3 and pad adn amine	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:22
17	254533	(sun.in. li.in. redeker.in) and CU and CMP and polish$3 and pad adn amine and organic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:22
18	12132	(sun.in. li.in. redeker.in) and CU and CMP and polish$3 and pad adn amine and organic and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:23
19	13	(sun.in. li.in. redeker.in) and CU and CMP and polish$3 and pad and amine and organic and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/18 12:23
-	0	"cu cmp polishing pad cleaning".ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 07:10
-	1	"cu cmp polishing".ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/08 18:28
-	0	cu near3 cmp near3 polishing near3 pad near3 cleaning	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 14:02
-	5	sun.in. & li.in. & redeker.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/08 18:35
-	0	"REMOVING TONER FROM PRINTED MATERIAL".ti.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/08 18:35
-	0	"REMOVING TONER FROM PRINTED MATERIAL"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/06/08 18:35
-	28881	(amine amide) and ("ph 5" "ph 6" "ph 7" "ph 8" "ph 9" "ph 9" "ph 10" "ph 11" "ph 12") and organic and (acid base)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 07:43
-	4278	((amine amide) and ("ph 5" "ph 6" "ph 7" "ph 8" "ph 9" "ph 9" "ph 10" "ph 11" "ph 12") and organic and (acid base)) and ethylenediamine and (phosphoric acetic sulfuric potassium sodium ammonium) near5 (acid hydroxide) and (DI dionized water)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 07:19

-	10	((((amine amide) and ("ph 5" "ph 6" "ph 7" "ph 8" "ph 9" "ph 9" "ph 10" "ph 11" "ph 12") and organic and (acid base)) and ethylenediamine and (phosphoric acetic sulfuric potassium sodium ammonium) near5 (acid hydroxide) and (DI dionized water)) and (copper cu) and (cmp "chemical mechanical polishing")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 07:21
-	12	(amine amide) and ("ph 5" "ph 6" "ph 7" "ph 8" "ph 9" "ph 9" "ph 10" "ph 11" "ph 12") and organic and (acid base) and (cmp "chemical mechaical") and rins$4 and clean$4 and wafer	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 07:48
-	11	"163582"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 07:49
-	5	"359141"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 07:51
-	53	"46353"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 07:53
-	0	"99/46353"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 07:53
-	0	99/46353	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/07/23 07:53
-	0	(copper cu) near3 cmp near3 polishing near3 pad near3 clean$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 14:22
-	1638	small.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 14:22
-	60	small.in. and clean	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 14:26
-	8	small.in. and clean and pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 14:26
-	21	small.in. and clean$4 and pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 14:33
-	478	cmp and polish$4 and method and second$4 and clean$4 and pad and (cu copper) and solution	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 14:42

-	90	cmp and polish$4 and method and second$4 and clean$4 and pad and (cu copper) and solution and amin$4	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 14:44
-	8	small.in. and clean and pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 16:05
-	21328	small.in. and clean and pad diamine and acetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 16:23
-	2	small.in. and clean and pad and diamine and acetic	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 16:05
-	2458	water and cmp and clean and pad $6amine and acetic and method and wafer and surface	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 16:26
-	3216	(diw water) and cmp and clean$4 and pad (amine $6amine)and method and wafer and surface and organic and (cu copper)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 16:27
-	3216	(diw water) and cmp and clean$4 and pad (amine $6amine)and method and wafer and surface and organic and (cu copper) and ((diw water) and cmp and clean$4 and pad (amine $6amine)and method and wafer and surface and organic and (cu copper))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 16:28
-	1072	(diw water) and cmp and clean$4 and pad (amine)and method and wafer and surface and organic and (cu copper) and ((diw water) and cmp and clean$4 and pad (amine $6amine)and method and wafer and surface and organic and (cu copper)) and clean$4 near5 pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 16:29
-	11	(diw water) and cmp and clean$4 and pad and amine and method and wafer and surface and organic and (cu copper) and ((diw water) and cmp and clean$4 and pad (amine $6amine)and method and wafer and surface and organic and (cu copper)) and clean$4 near5 pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 16:41
-	3	("5,616,069").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 16:39
-	11	(diw water) and cmp and amine and method and wafer and surface and organic and (cu copper) and clean$4 near5 pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/05 16:42
-	11	(diw water) and cmp and (hydroxylamine amine) and method and wafer and surface and organic and (cu copper) and clean$4 near5 pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 06:32
-	40	(diw water "DI water") and cmp and method and wafer and surface and RPM and (rate ml/min delivery) and rins$4 and (condition clean$4) near5 pad	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 06:55

-	.	11	(diw water "DI water") and cmp and method and wafer and surface and RPM and (rate ml/min delivery) and rins$4 and (condition clean$4) near5 pad and ml/min	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/06 06:57
-		11	(diw water "DI water") and cmp and method and wafer and surface and RPM and (rate ml/min delivery) and rins$4 and (condition clean$4) near5 pad and (ml/min mI/min)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/08 06:36
-		0	placing near5 polished near5 semiconductor near5 substrate near5 scrubber and li.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/08 06:37
-		0	placing near5 polished near5 semiconductor near5 substrate near5 scrubber	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/08 06:38
-		19821	rincoln delarios.in. semiconductor and clean and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/08 06:39
-		0	rincoln and delarios.in. and semiconductor and clean and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/08 06:39
-		8	delarios.in. and semiconductor and clean and substrate	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/08 07:44
-		2	"6352595"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/08 08:16
-		2	("6,280,299").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/08 08:17
-		2	("6,220,941").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/08 08:17
-		2	("6242079").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/08 13:58
-		0	(""aspect ratio" and copper and etch and adhesion and promotion").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/08 13:59
-		18	"aspect ratio" and copper and etch and adhesion and promotion .	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/08 14:00
-		17	"aspect ratio" and copper and etch and adhesion and promotion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/08 14:00

-	6	"aspect ratio" and copper and etch and adhesion and promotion and immersion	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/08 14:01
-	48	(("3889753") or ("4090563") or ("4541945") or ("4954142") or ("5084071") or ("5225034") or ("5340370") or ("5478436") or ("5527423") or ("5645682") or ("5662769") or ("5509970") or ("5876508") or ("5879226") or ("5981454") or ("6033993") or ("5830280")).PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 07:23
-	0	(("3889753") or ("4090563") or ("4541945") or ("4954142") or ("5084071") or ("5225034") or ("5340370") or ("5478436") or ("5527423") or ("5645682") or ("5662769") or ("5509970") or ("5876508") or ("5879226") or ("5981454") or ("6033993") or ("5830280")).PN.	US-PGPUB	2002/08/15 07:24
-	17	(("3889753") or ("4090563") or ("4541945") or ("4954142") or ("5084071") or ("5225034") or ("5340370") or ("5478436") or ("5527423") or ("5645682") or ("5662769") or ("5509970") or ("5876508") or ("5879226") or ("5981454") or ("6033993") or ("5830280")).PN.	USPAT	2002/08/15 14:41
-	1	((("3889753") or ("4090563") or ("4541945") or ("4954142") or ("5084071") or ("5225034") or ("5340370") or ("5478436") or ("5527423") or ("5645682") or ("5662769") or ("5509970") or ("5876508") or ("5879226") or ("5981454") or ("6033993") or ("5830280")).PN.) and (amine amide) and organic and pad and surface and clean	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 07:26
-	0	"09/163368"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 14:45
-	8	"163368"	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2002/08/15 14:46
-	2	("5,981,454").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/14 16:06
-	2	("6,280,299").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 06:45
-	3223	cu and cmp and ph and polish and clean composition and organic and amine and wafer and complex	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 06:47
-	3131	cu and cmp and ph near2 ("8" "11") and polish and clean composition and organic and amine and wafer and complex	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 06:48
-	8	cu and cmp and ph near2 ("8" "11") and polish and clean and composition and organic and amine and wafer and complex	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 06:54
-	891	polish$3 near3 pad near10 clean$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 06:55

-	31	polish$3 near3 pad near10 clean$3 and amine and complex	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 07:24
-	891	polish$3 near3 pad near10 clean$3	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 07:24
-	67	polish$3 near3 pad near10 clean$3 and cu and cmp	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 09:29
-	1		USPAT	2003/07/16 09:19
-	1		USPAT	2003/07/16 09:19
-	1		USPAT	2003/07/16 09:19
-	1		USPAT	2003/07/16 09:19
-	1		USPAT	2003/07/16 09:19
-	2	("6352595").PN.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM_TDB	2003/07/16 09:29
-	1		USPAT	2003/07/16 09:31
-	1		USPAT	2003/07/16 09:32
-	1		USPAT	2003/07/16 09:32
-	1		USPAT	2003/07/16 09:32
-	1		USPAT	2003/07/16 09:32
-	1		USPAT	2003/07/16 09:32
-	1		USPAT	2003/07/16 09:33
-	1		USPAT	2003/07/16 09:33
-	1		USPAT	2003/07/16 09:33
-	1		USPAT	2003/07/16 09:33
-	1		USPAT	2003/07/16 09:33
-	1		USPAT	2003/07/16 09:34
-	1		USPAT	2003/07/16 09:34
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